



Dickens
8/9/01

Docket No: 0756-2330

IN THE U.S. PATENT AND TRADEMARK OFFICE

IN RE PATENT APPLICATION OF:) Art Unit: 2823
Shunpei YAMAZAKI et al) Ex.: B. Kebede
SERIAL NO. 09/894,125)
FILED: 06/29/2001)
FOR: CRYSTALLINE SEMICONDUCTOR)
THIN FILM, METHOD OF)
FABRICATING THE SAME,)
SEMICONDUCTOR DEVICE AND)
METHOD OF FABRICATING THE SAME)

PRELIMINARY AMENDMENT

Honorable Commissioner for Patents
U.S. Patent and Trademark Office
Washington, D.C. 20231

Sir:

Please preliminarily amend the above identified patent application as follows:

In the Claims:

Please add the following new claims 19-26:

19. (New) A method of manufacturing a semiconductor device comprising the steps of:

- forming a semiconductor film comprising silicon over a substrate;
- irradiating said semiconductor film with laser light in an atmosphere containing oxygen for crystallizing said semiconductor film;
- removing an oxide film from a surface of the semiconductor film by etching after the irradiation of the laser light; and